

FIG. 1D

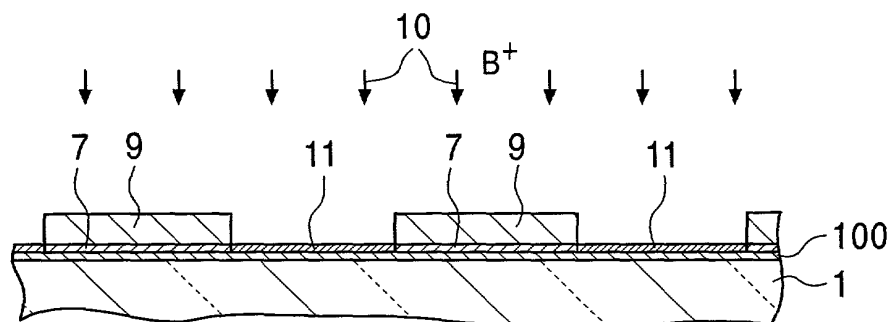


FIG. 1E

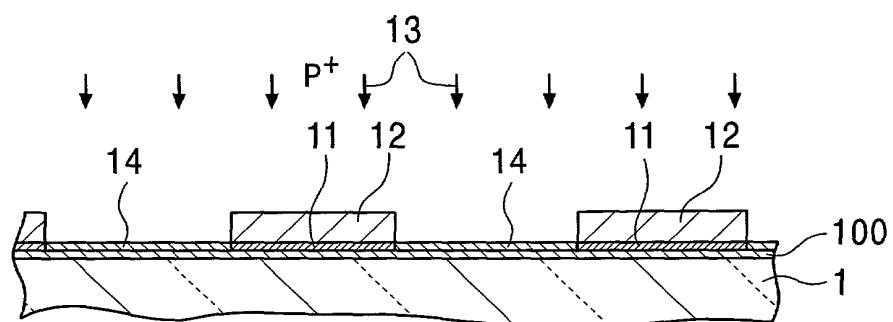


FIG. 1F

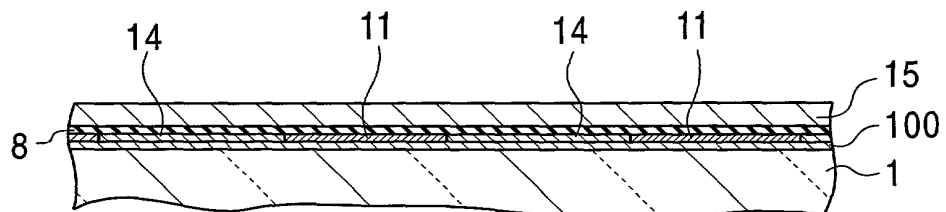


FIG. 1G

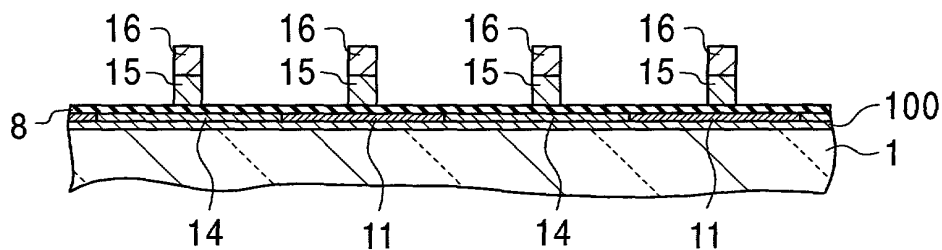


FIG. 1H

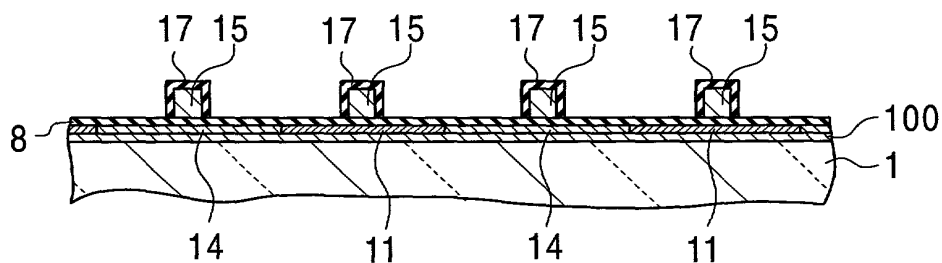


FIG. 1I

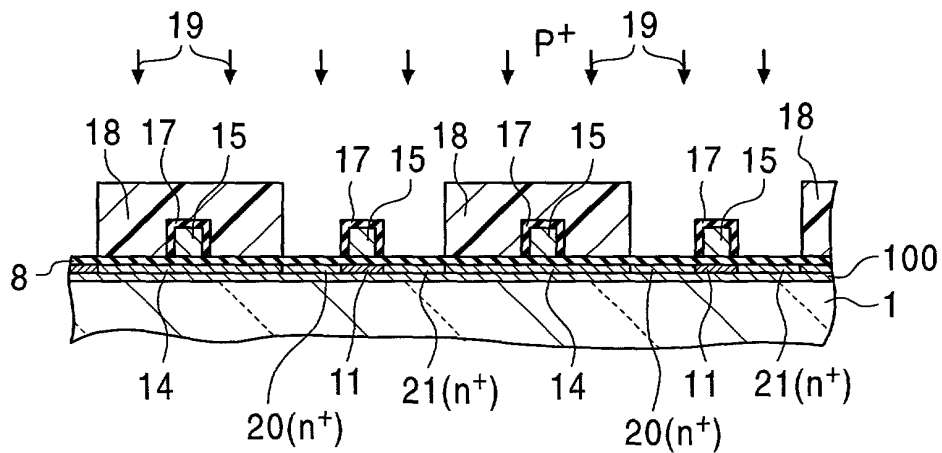


FIG. 1J

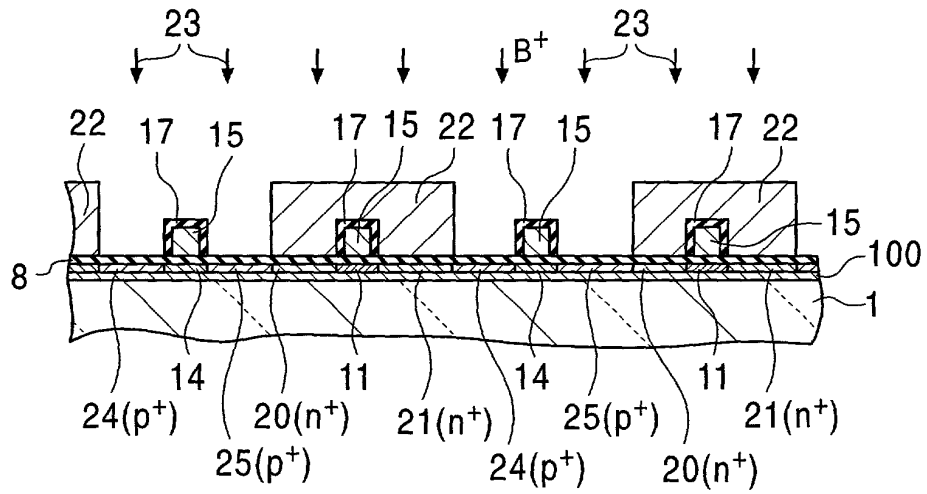


FIG. 1K

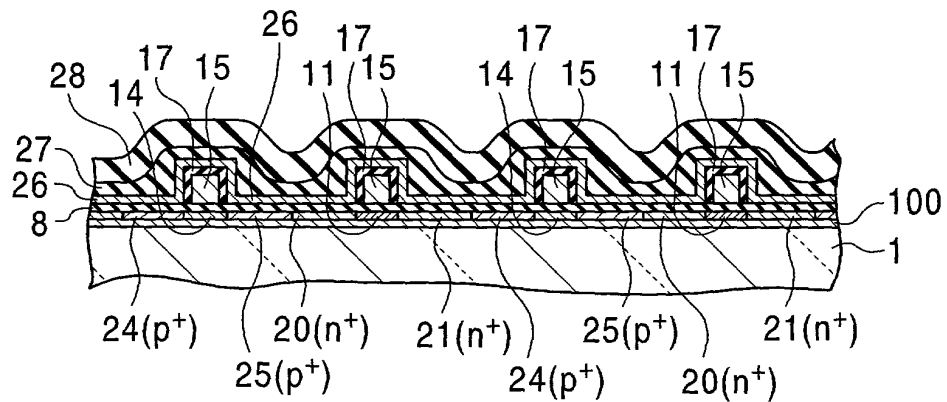


FIG. 1L

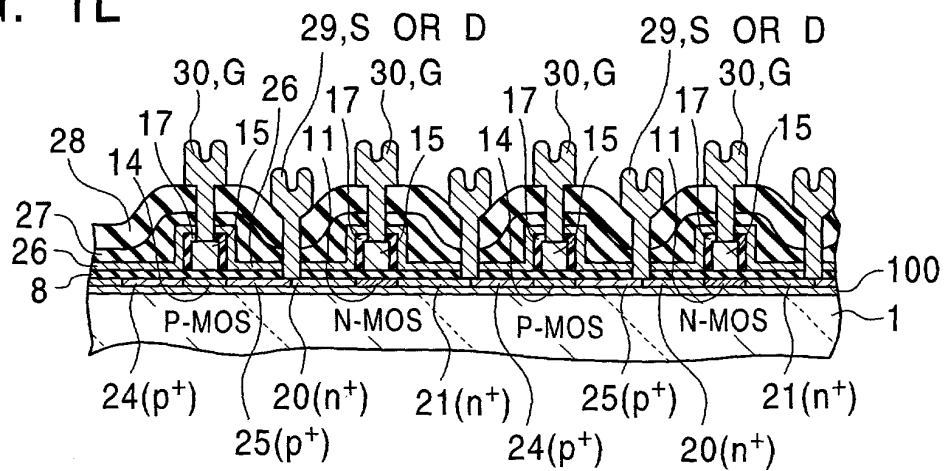


FIG. 2

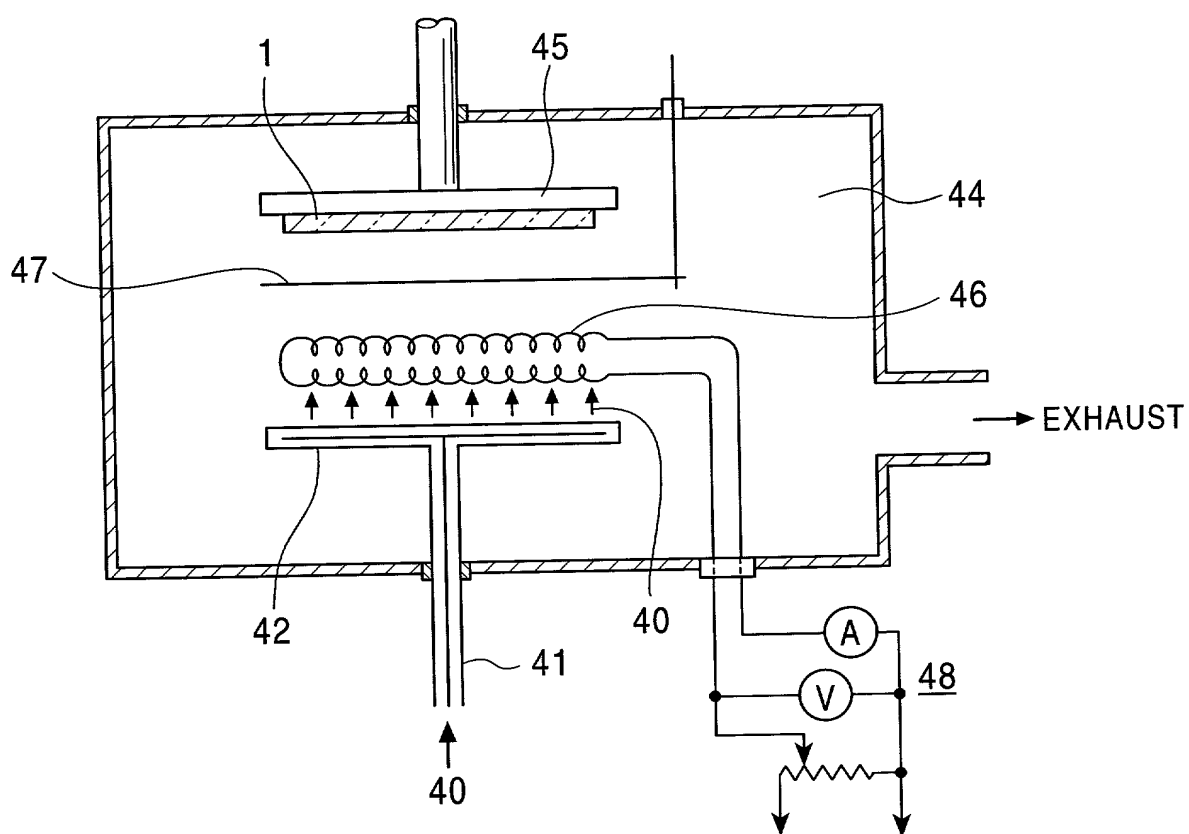
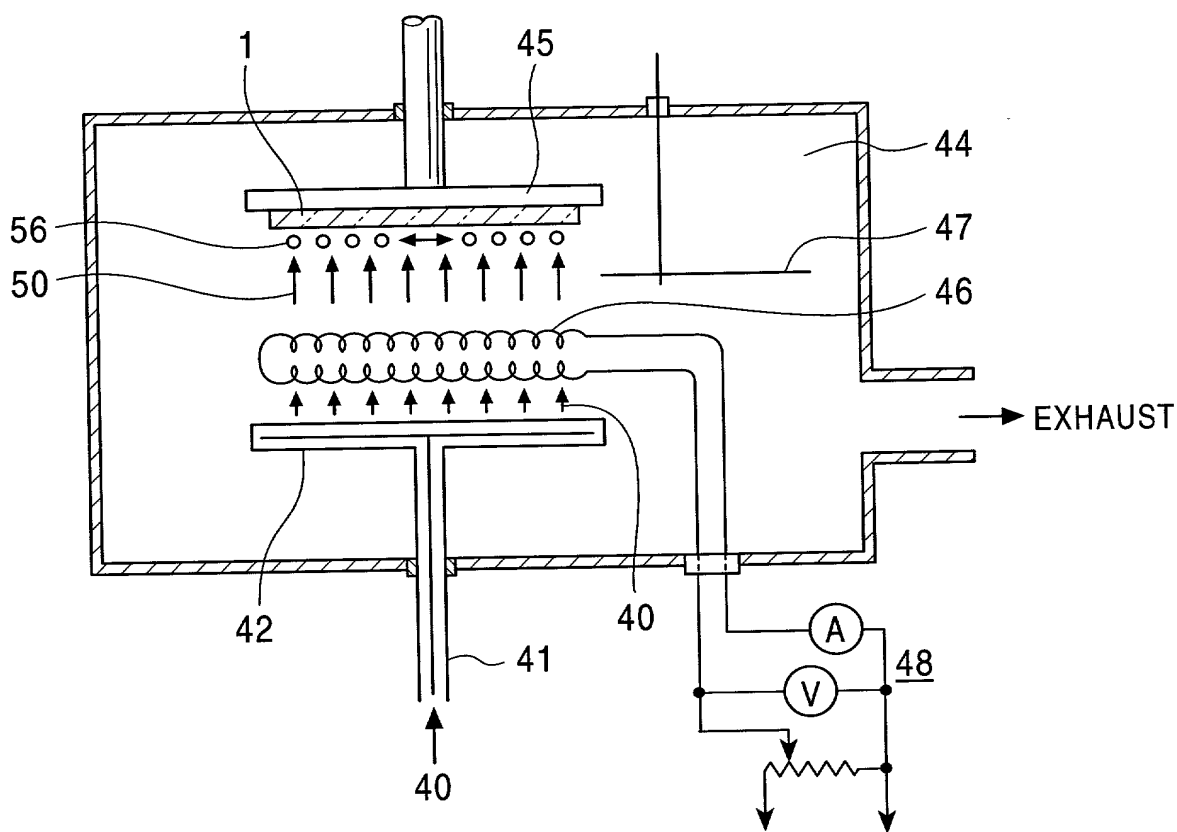


FIG. 3



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FIG. 4A

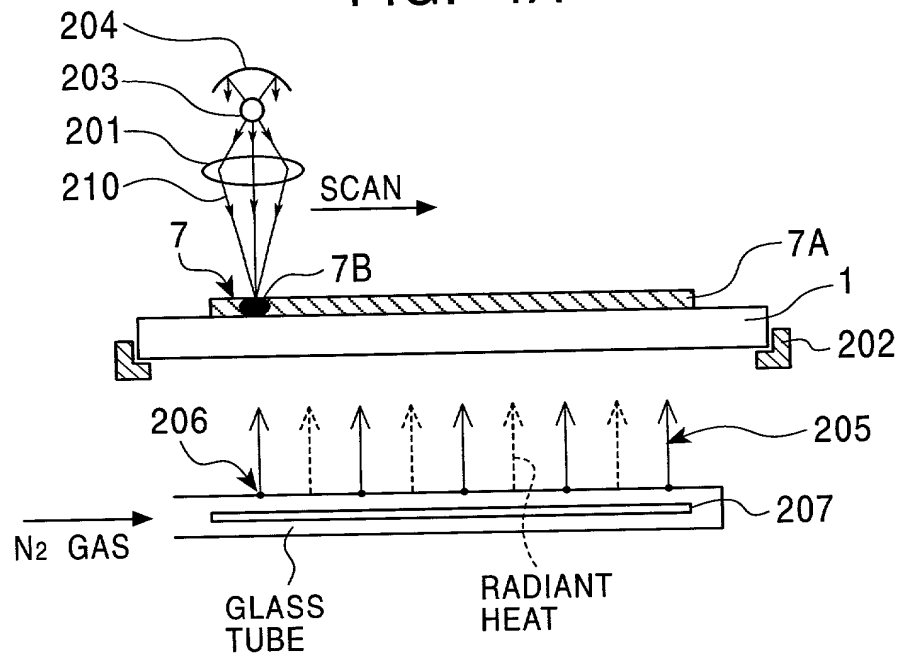


FIG. 4B

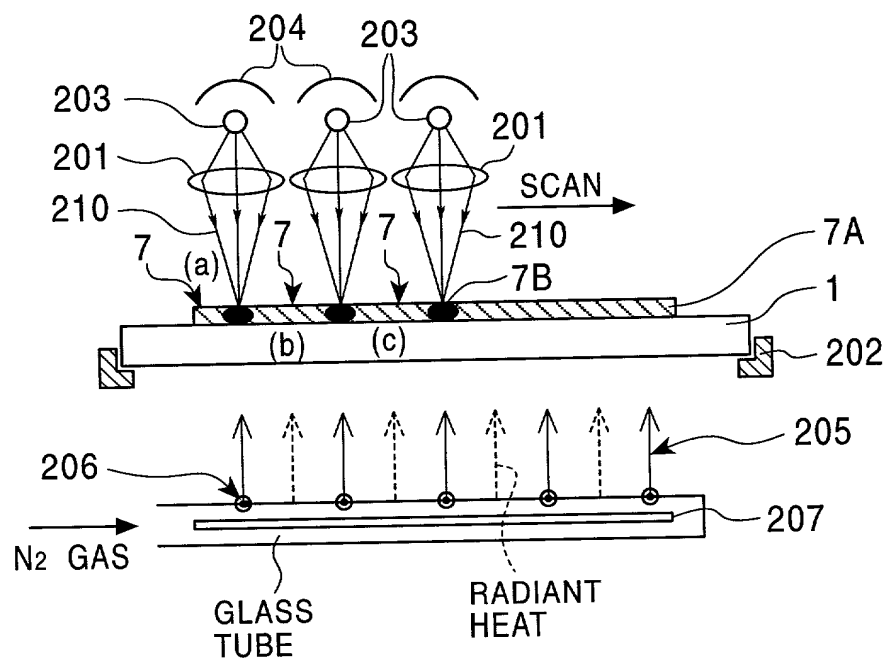


FIG. 4C

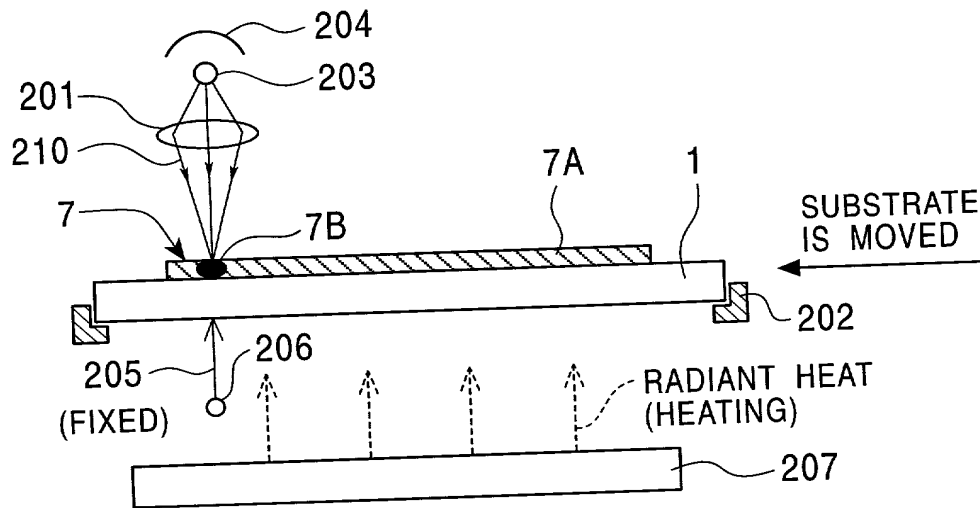


FIG. 4D

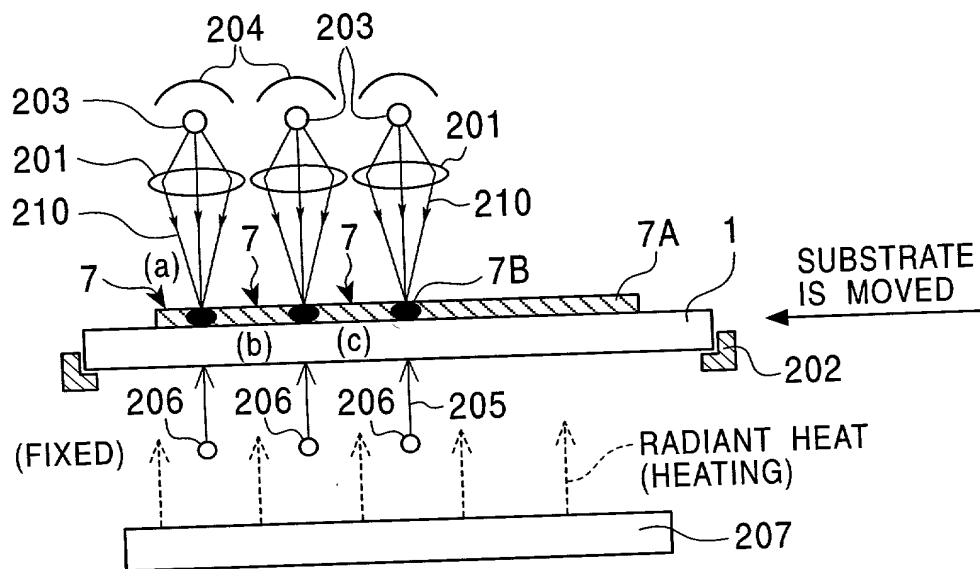


FIG. 5

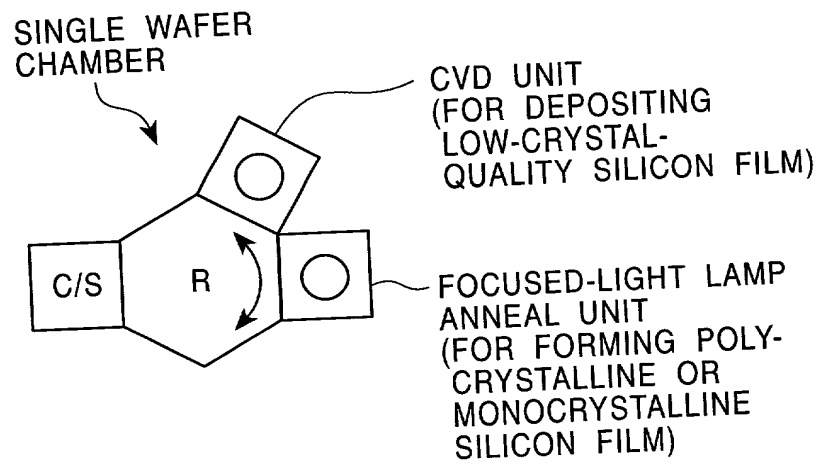


FIG. 6A

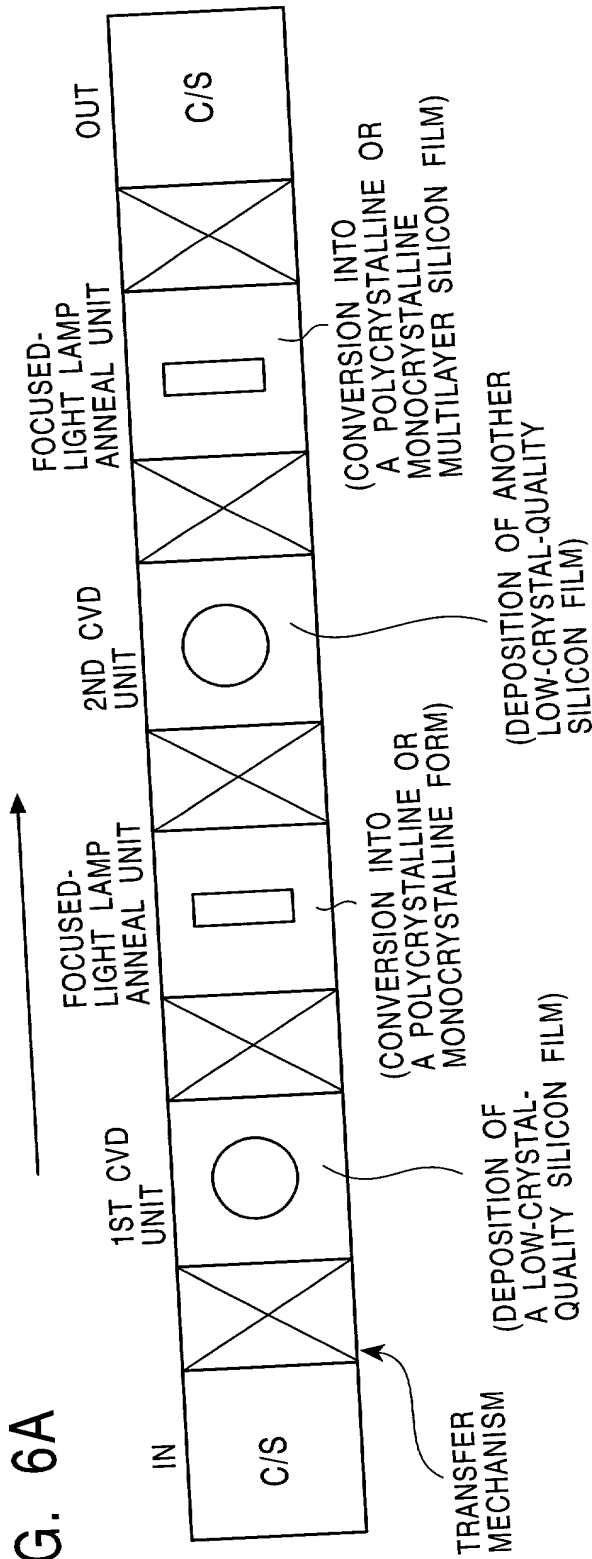


FIG. 6B

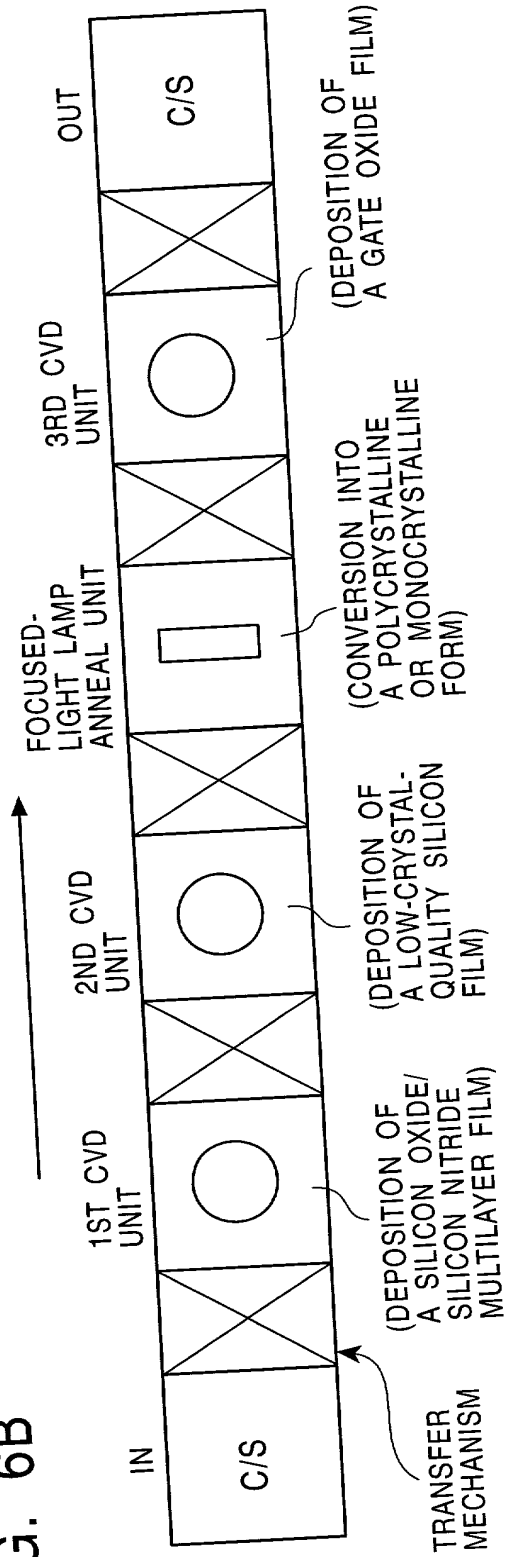


FIG. 7

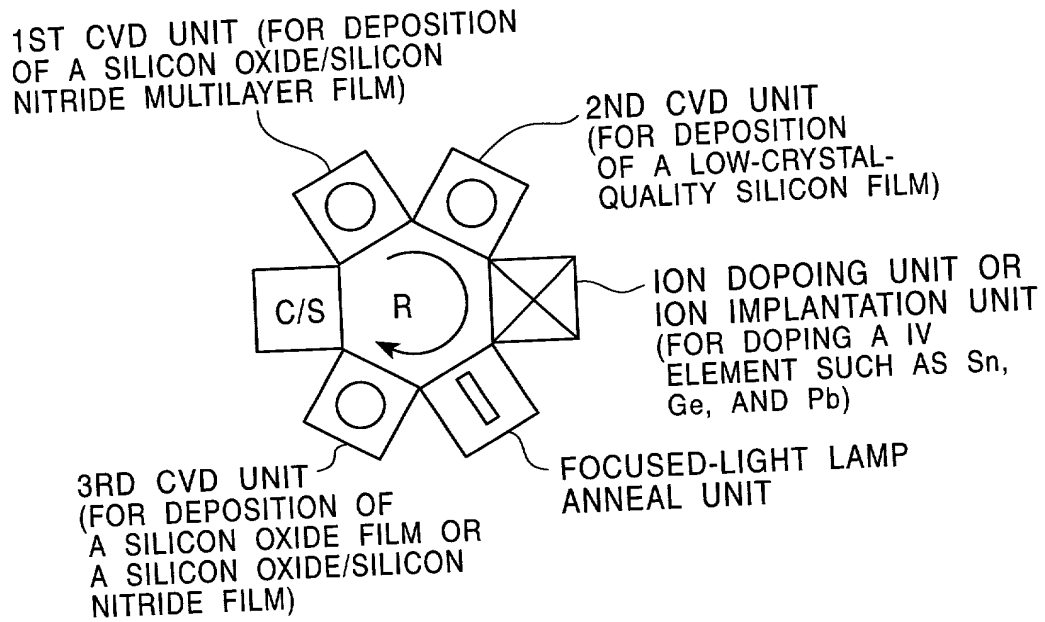


FIG. 8

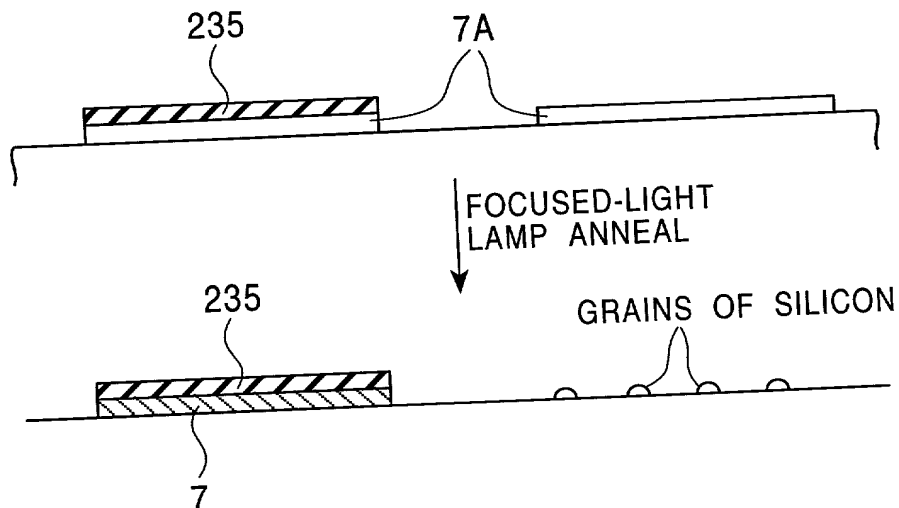


FIG. 9A

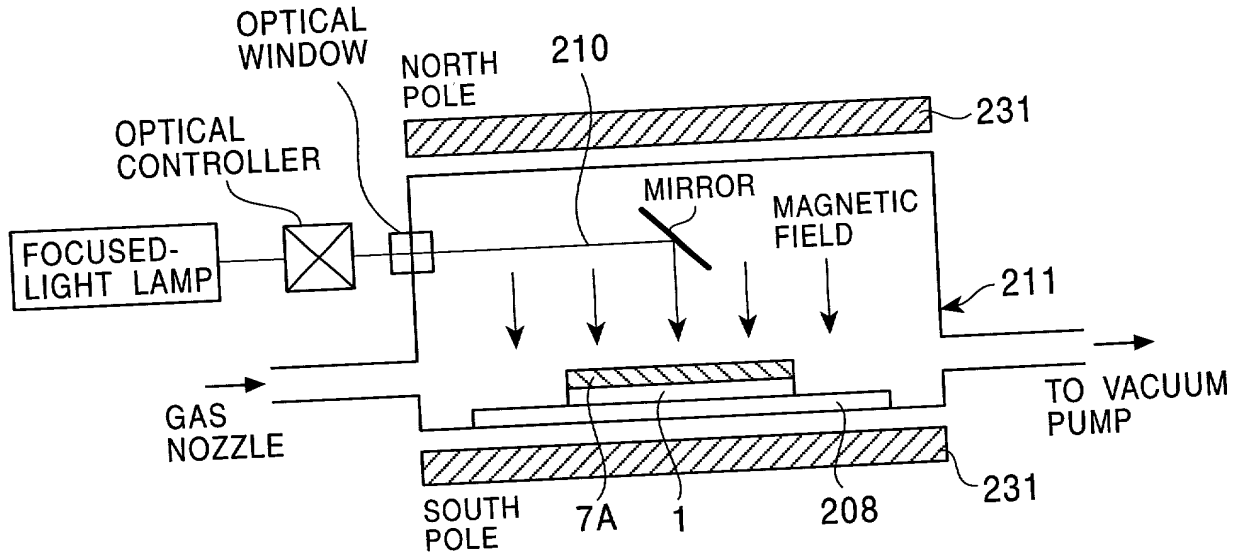


FIG. 9B

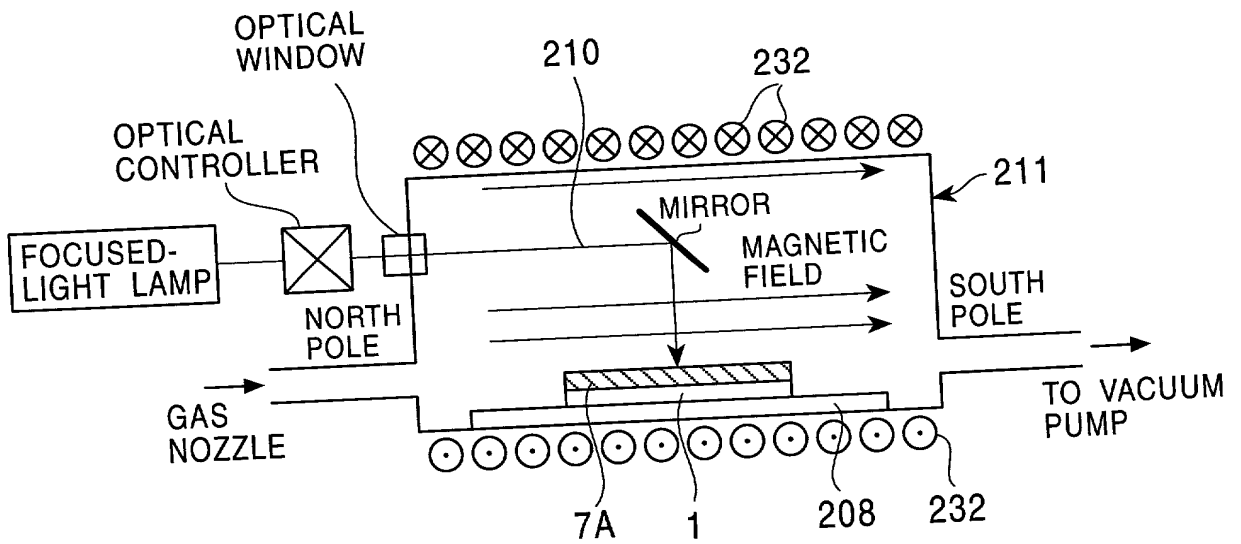


FIG. 9C

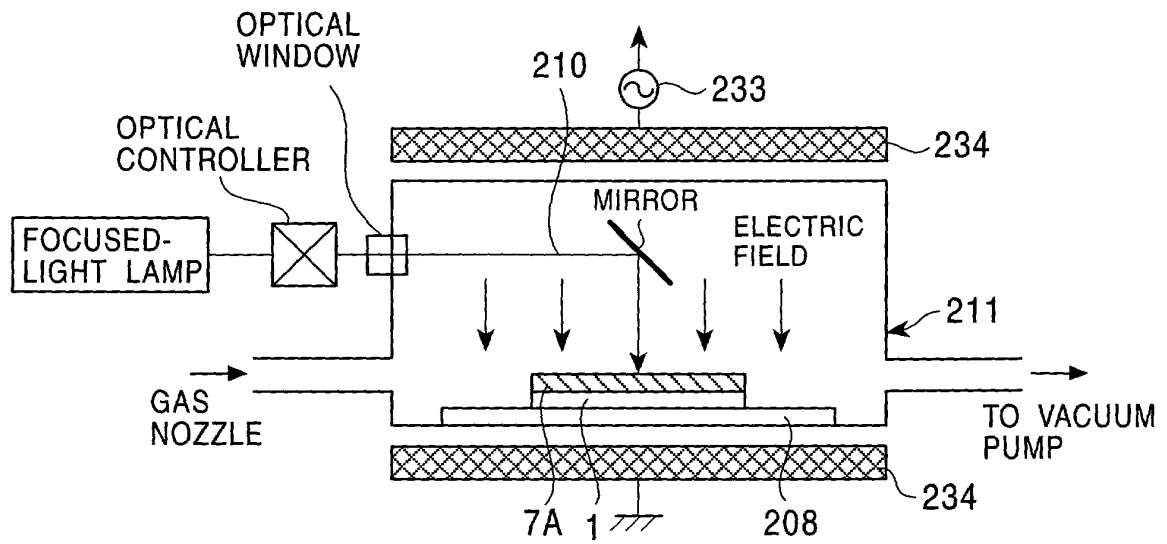


FIG. 9D

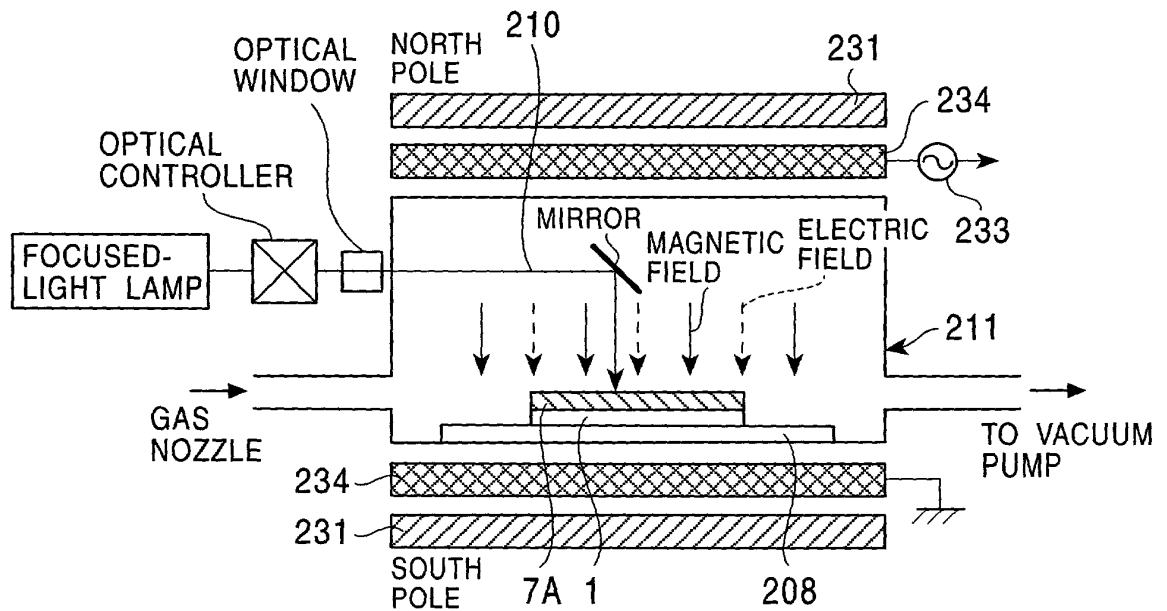


FIG. 10A

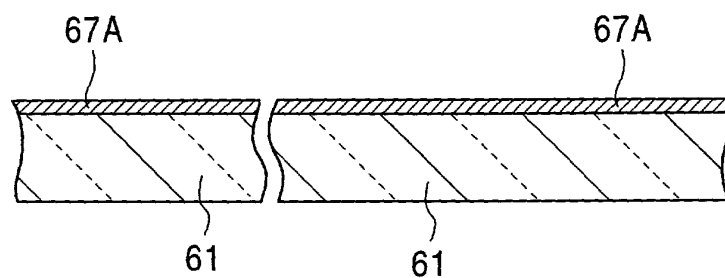


FIG. 10B

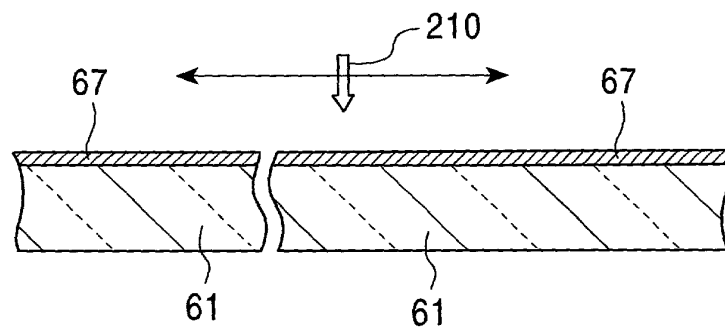


FIG. 10C

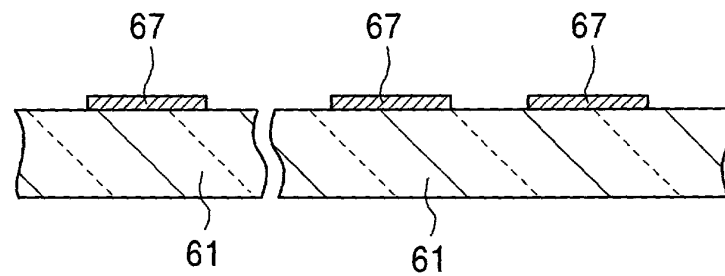


FIG. 10D

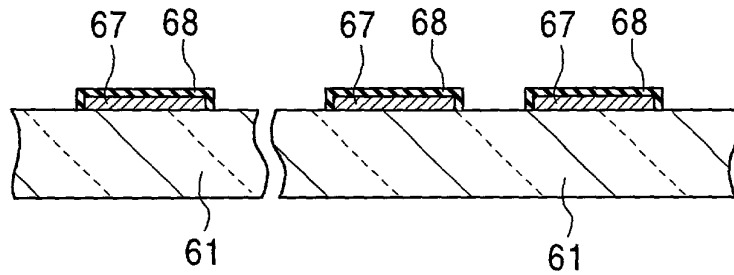


FIG. 10E

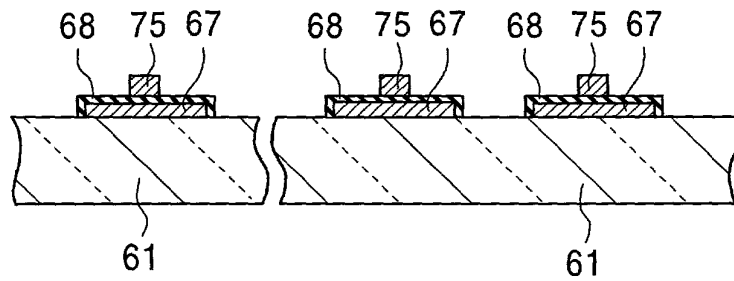


FIG. 10F

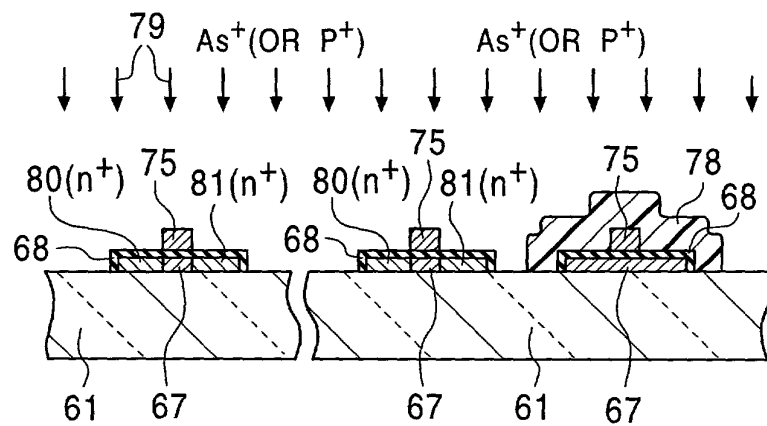


FIG. 10G

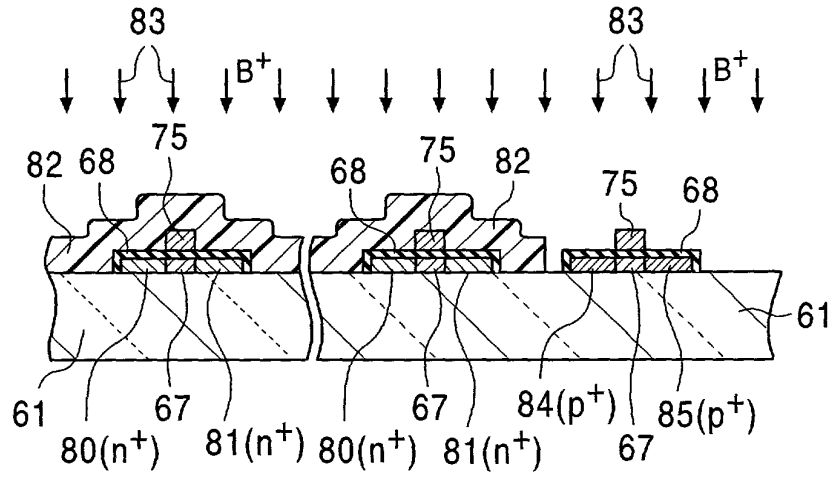


FIG. 10H

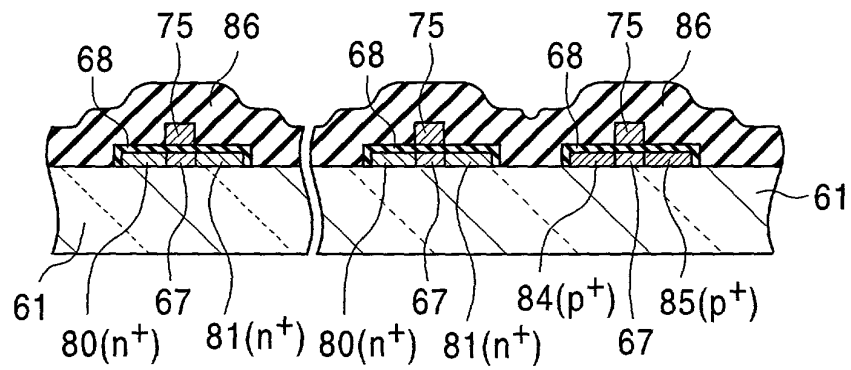


FIG. 10I

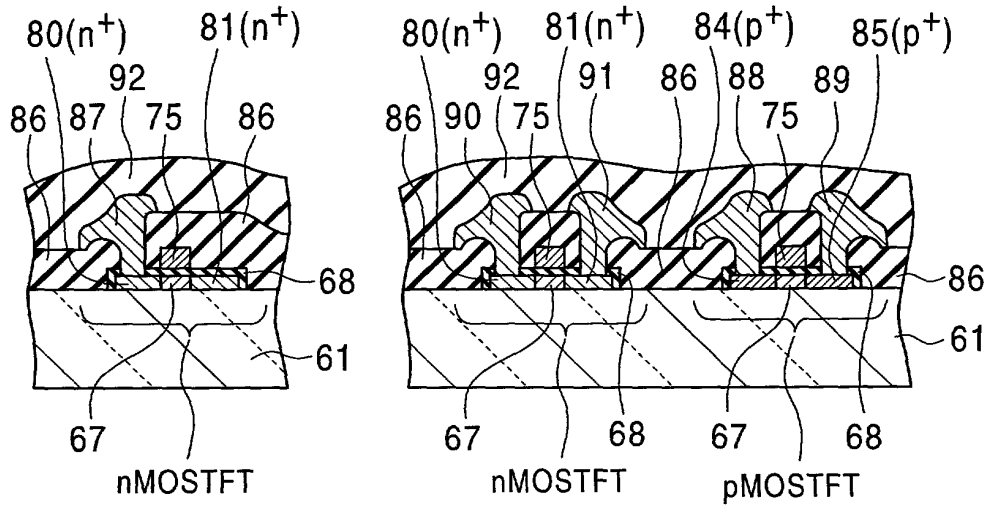


FIG. 10J

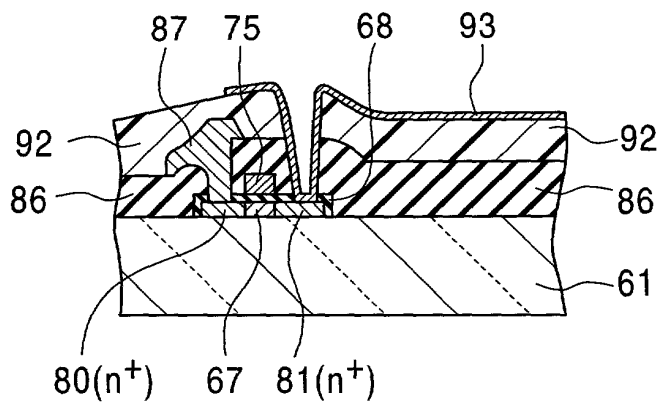


FIG. 10L

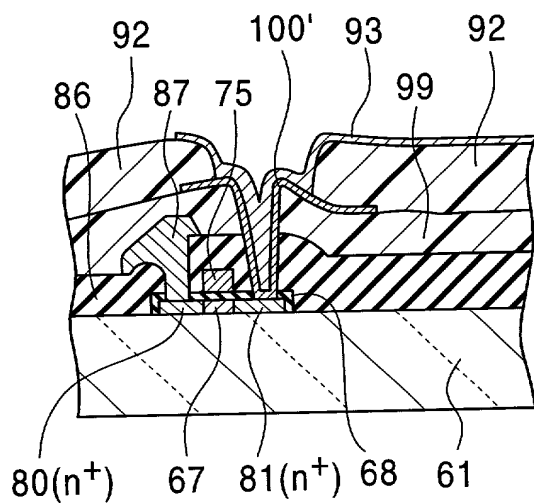
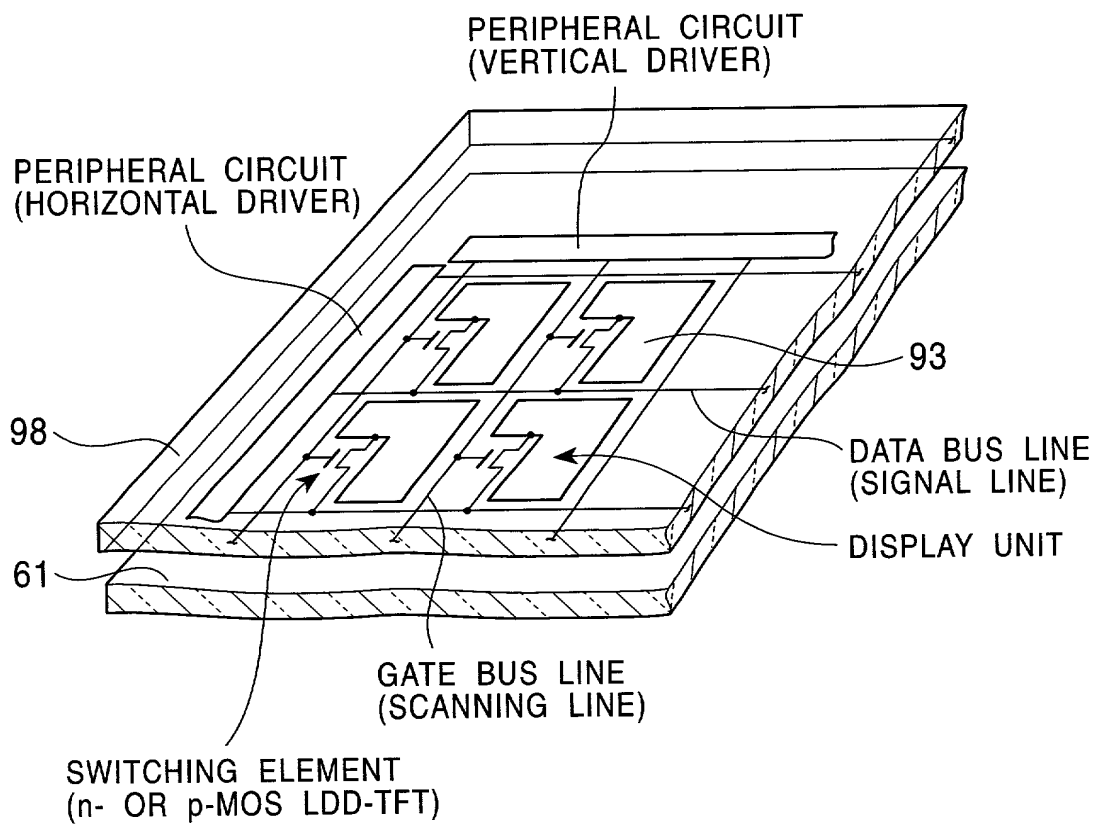


FIG. 11



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FIG. 12

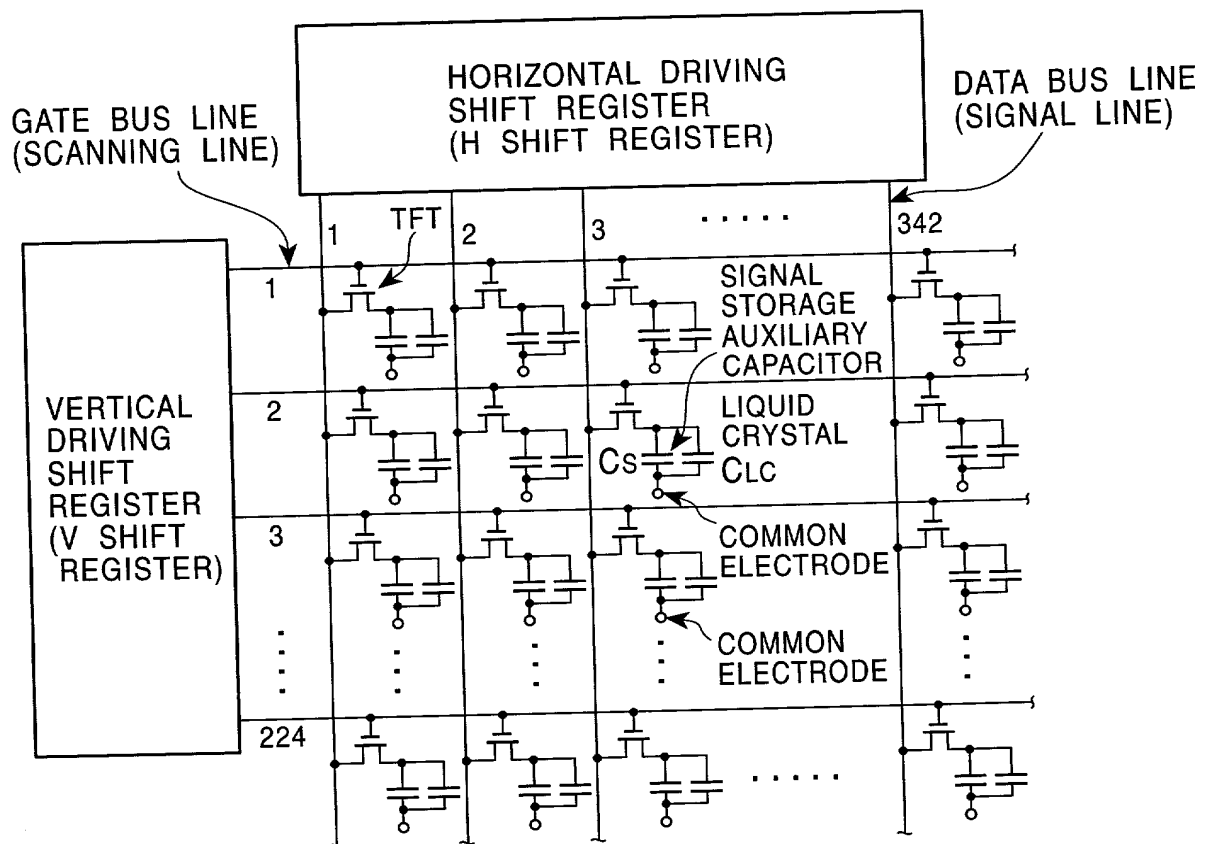


FIG. 13A

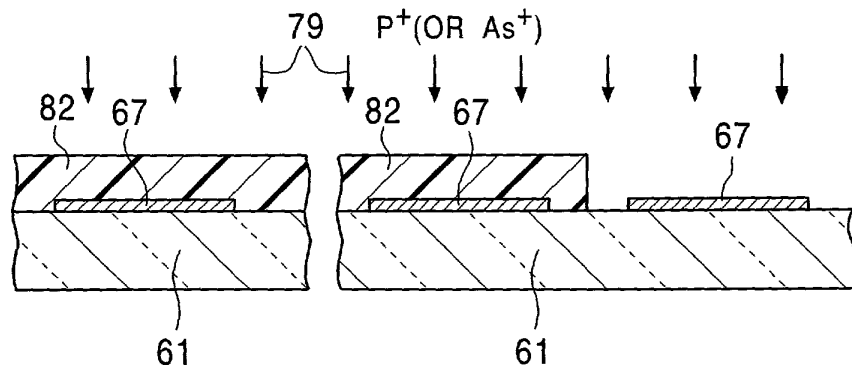


FIG. 13B

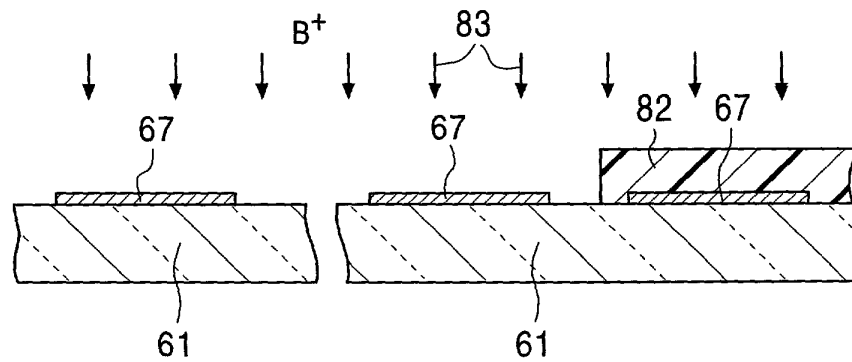


FIG. 13C

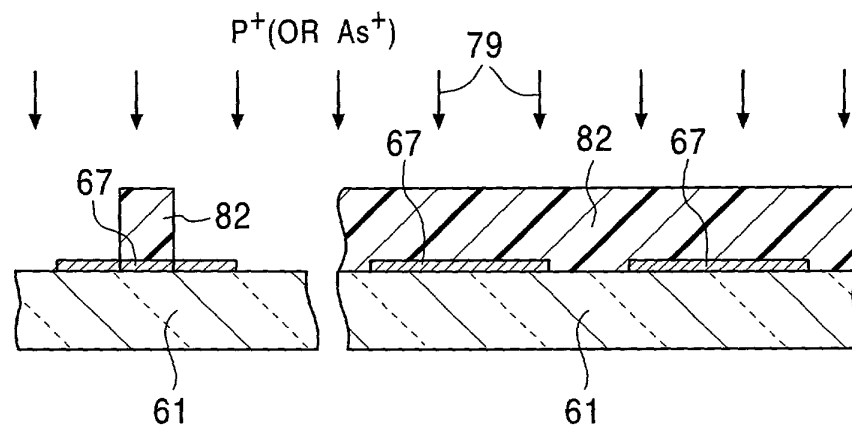


FIG. 13D

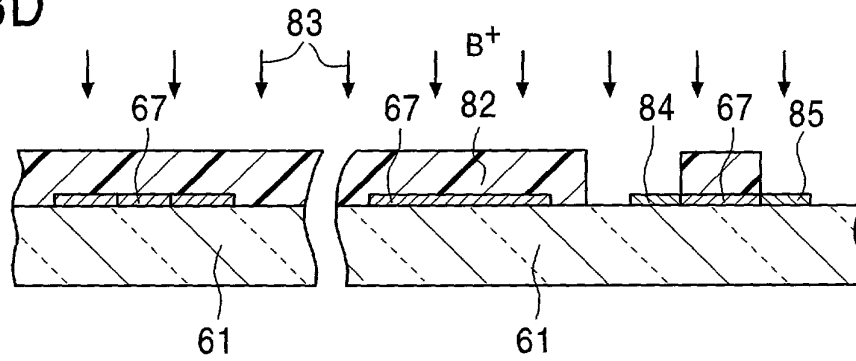


FIG. 13E

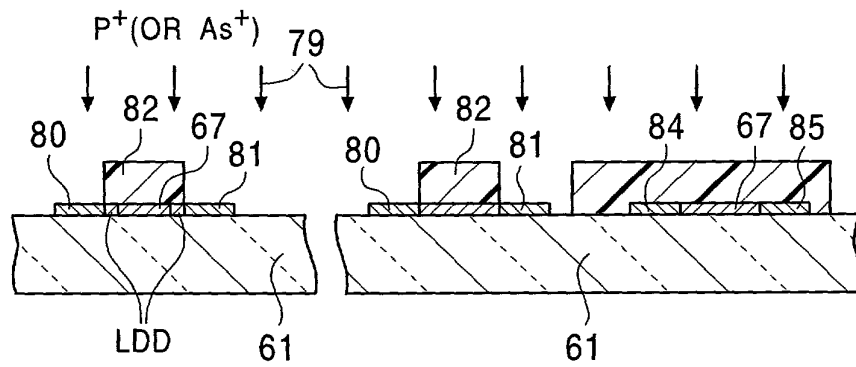


FIG. 13F

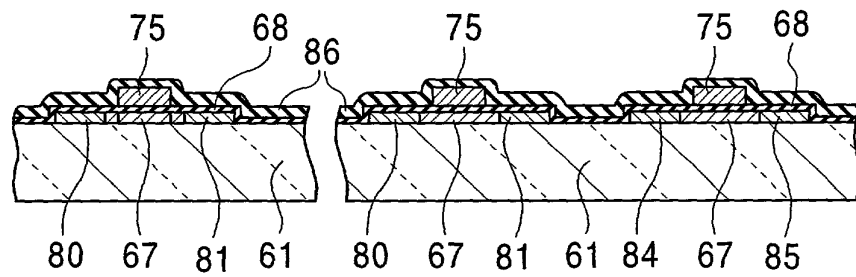
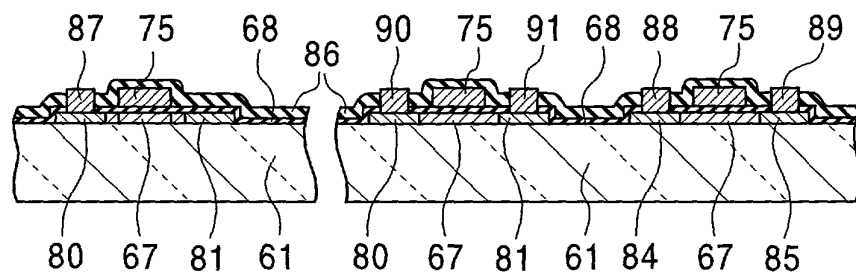


FIG. 13G



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FIG. 14A

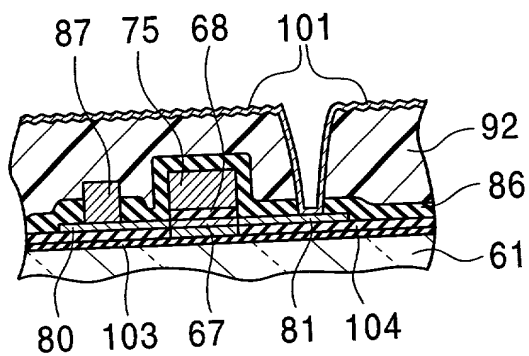


FIG. 14B

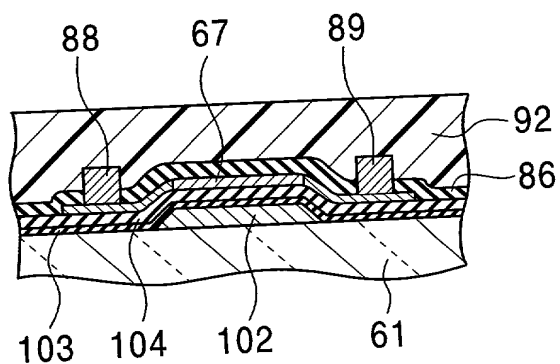
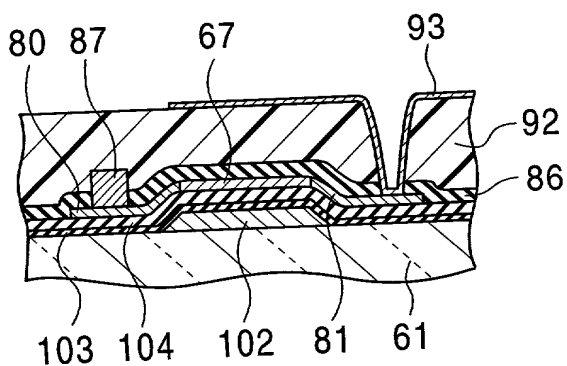


FIG. 14C

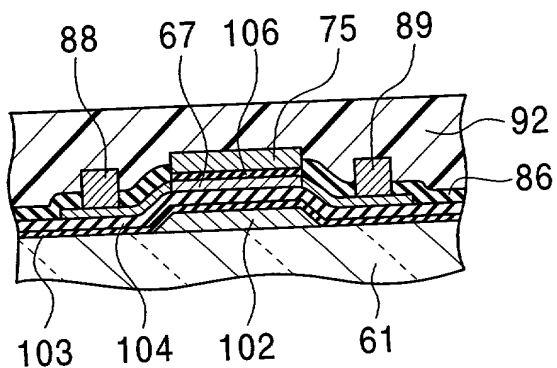
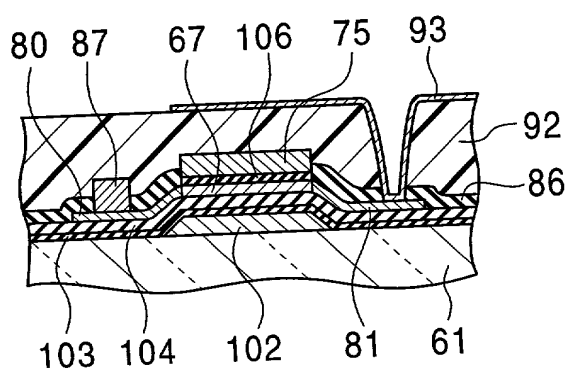


FIG. 15A

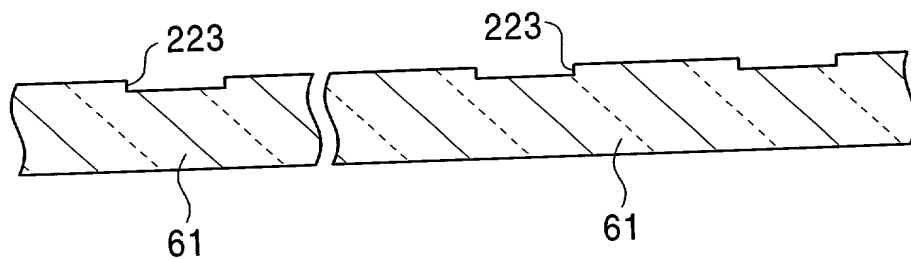


FIG. 15B

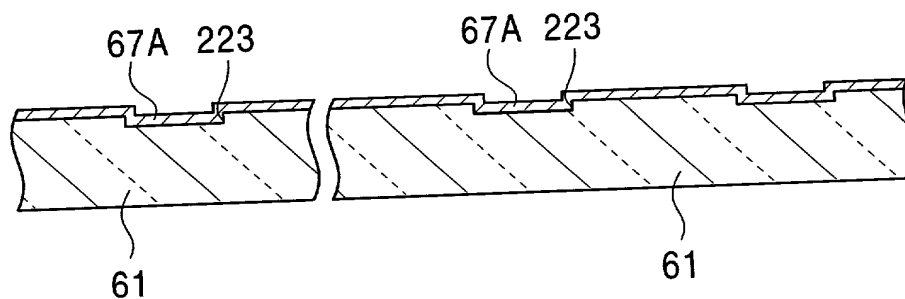
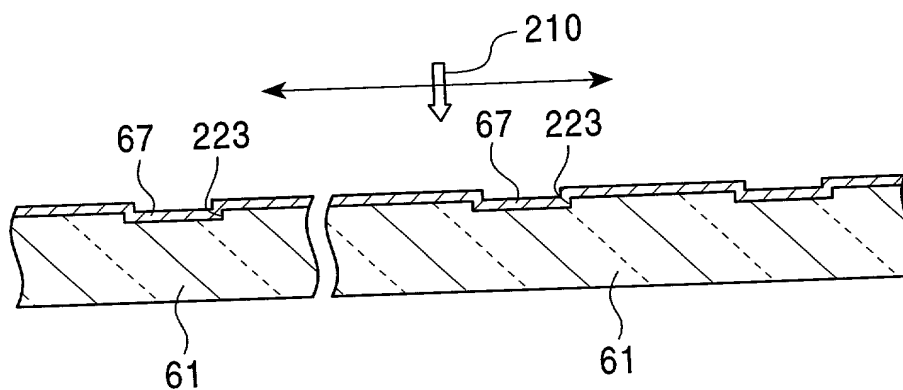


FIG. 15C



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FIG. 16A

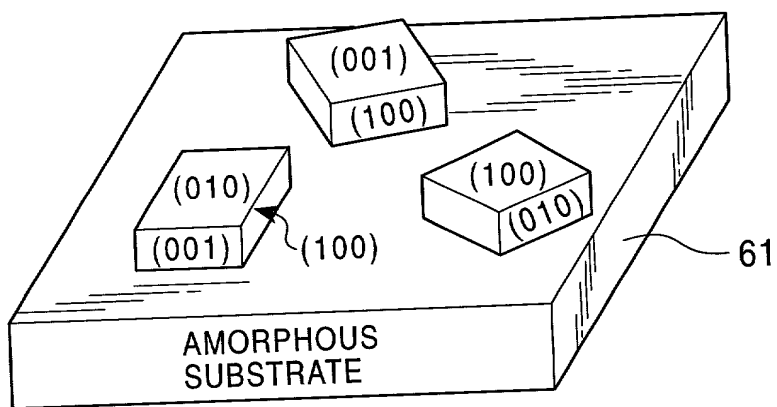


FIG. 16B

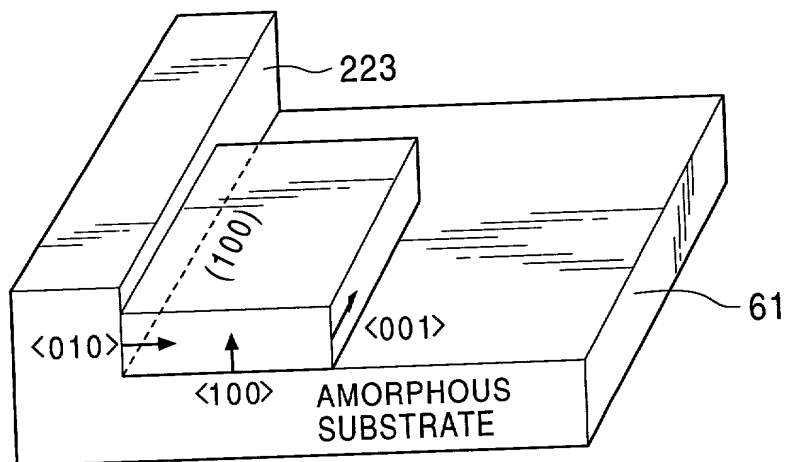


FIG. 17A

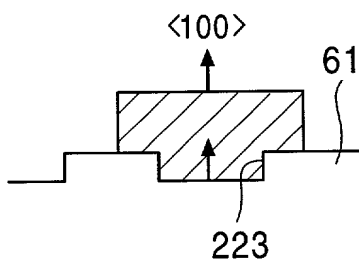


FIG. 17B

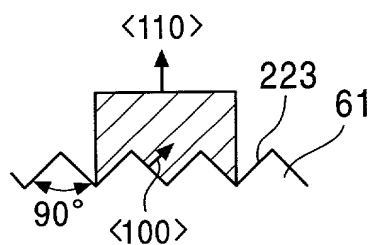


FIG. 17C

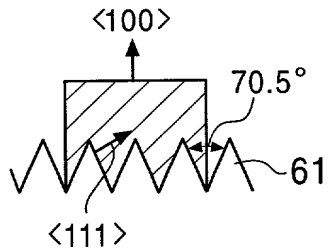


FIG. 17D

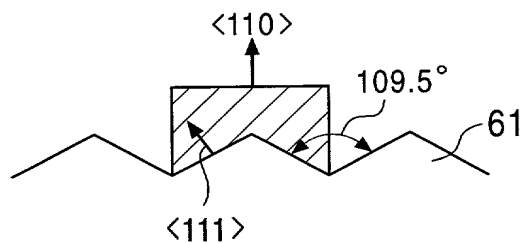


FIG. 17E

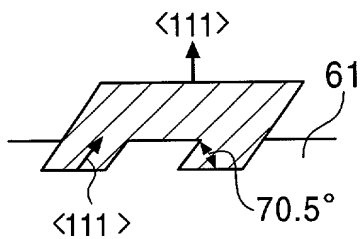
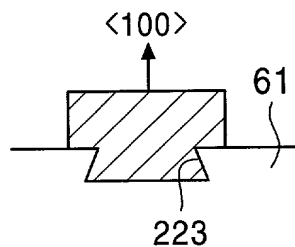


FIG. 17F



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FIG. 18A

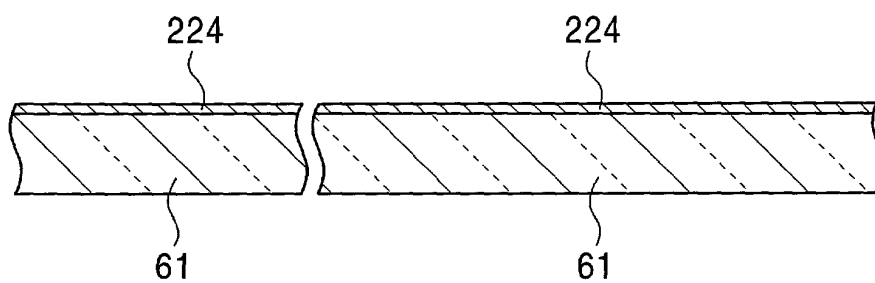


FIG. 18B

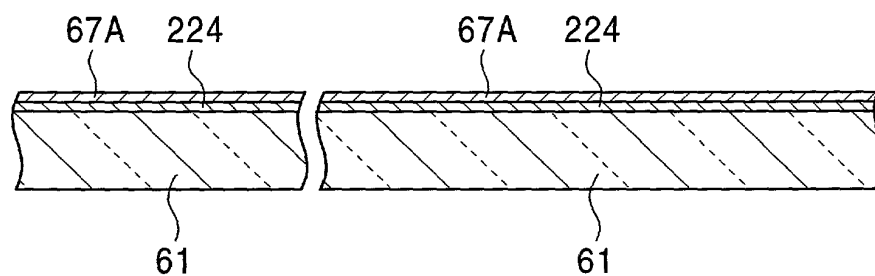
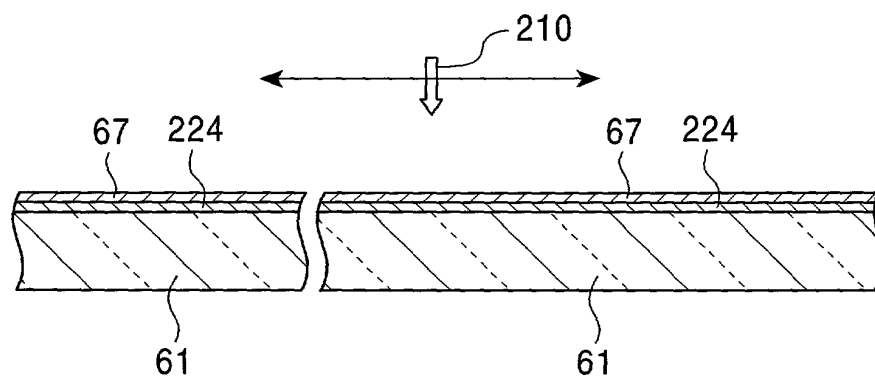


FIG. 18C



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FIG. 19A

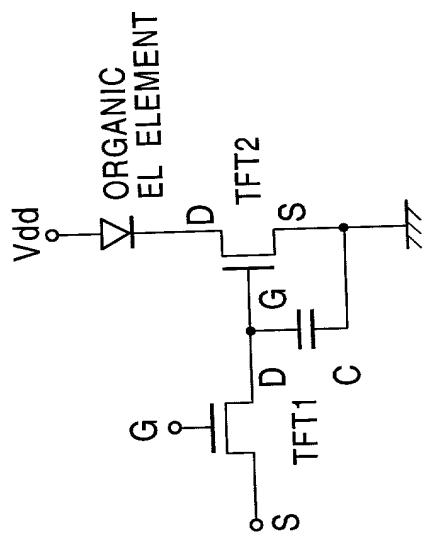


FIG. 19C

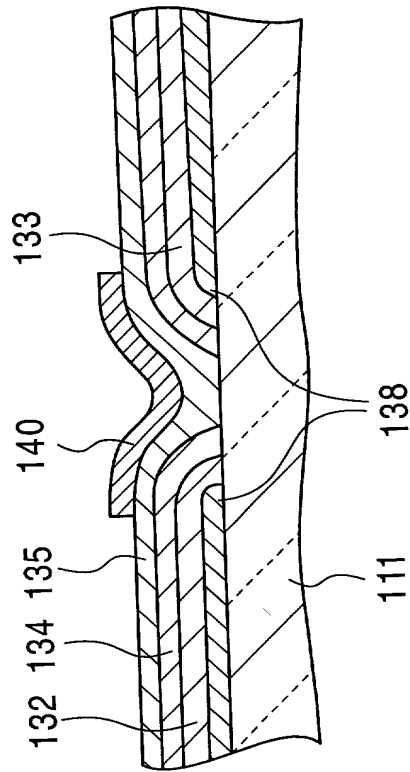


FIG. 19B

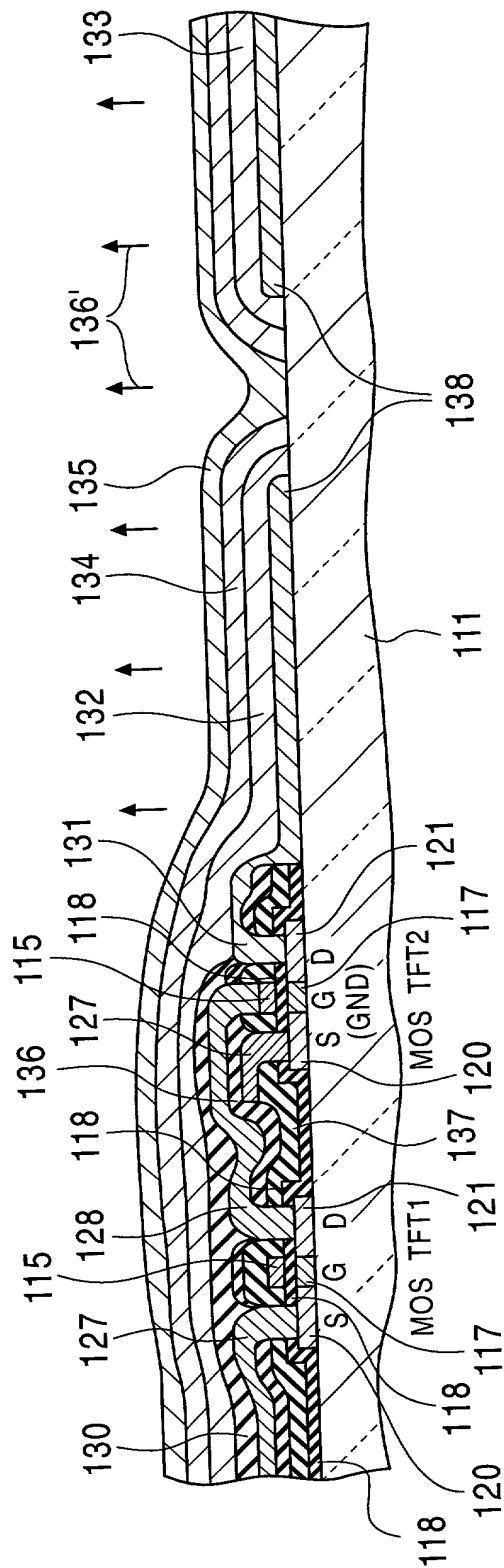


FIG. 20B

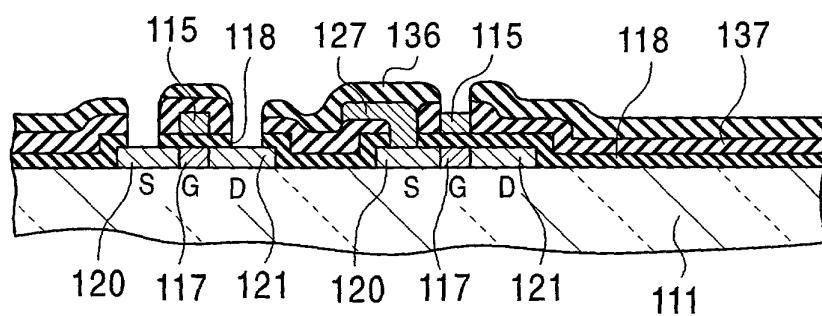


FIG. 20D

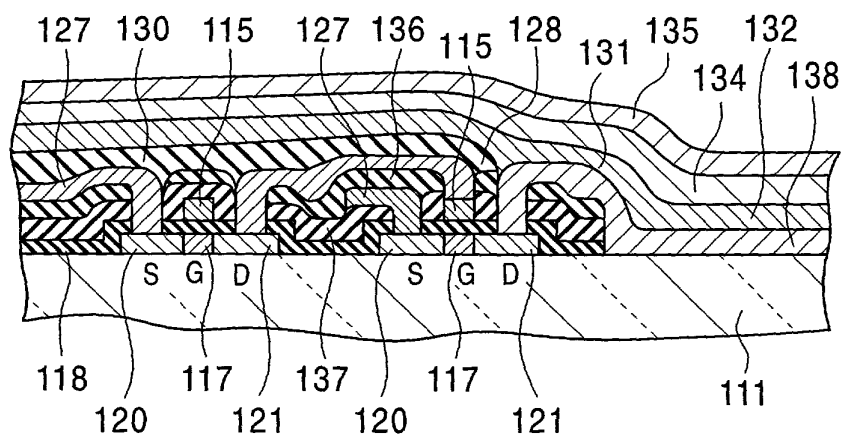


FIG. 21A

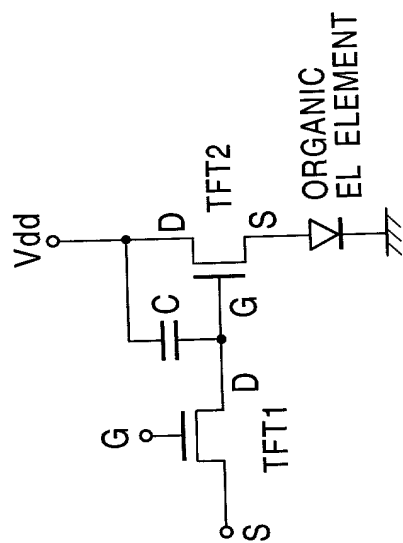


FIG. 21C

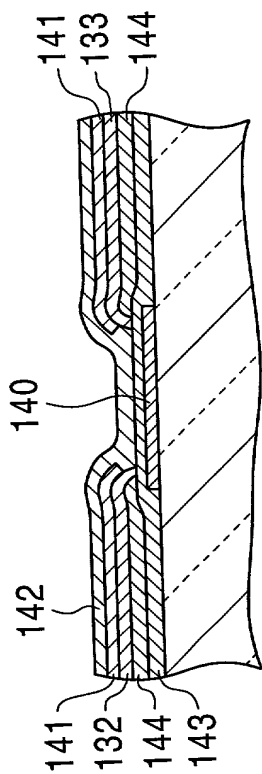


FIG. 21B

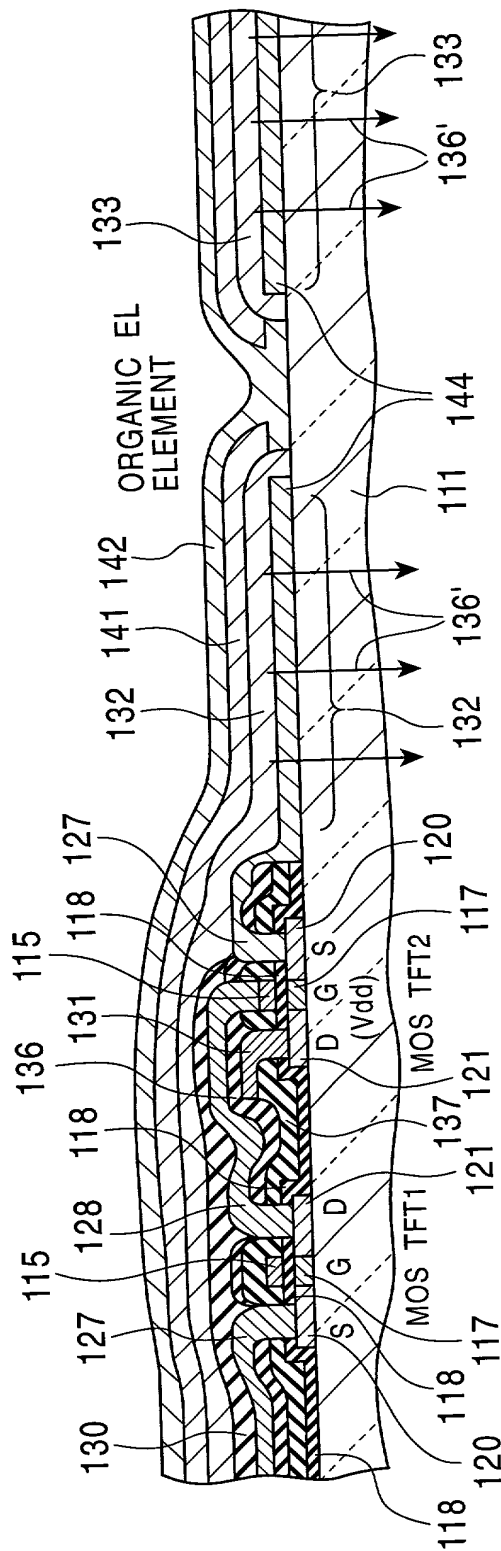


FIG. 22A

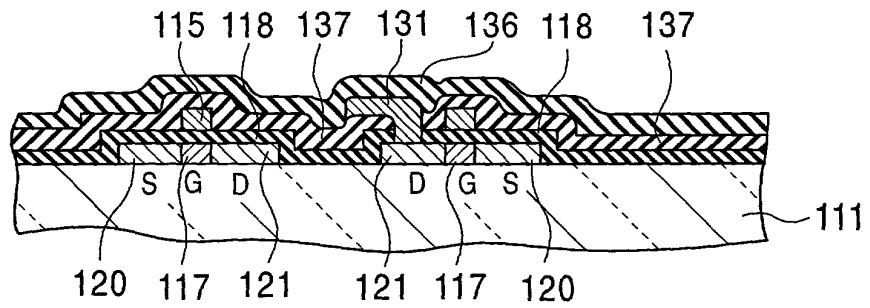


FIG. 22B

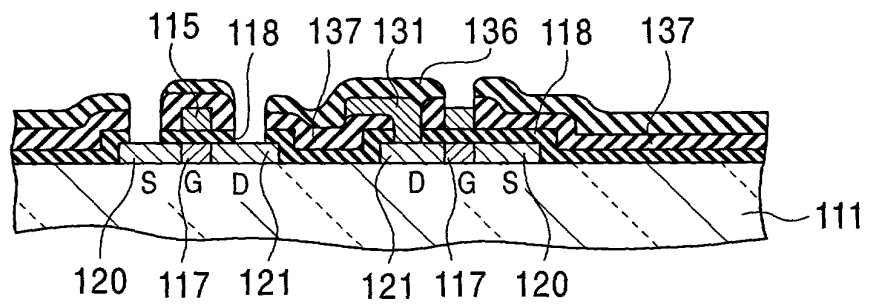


FIG. 22C

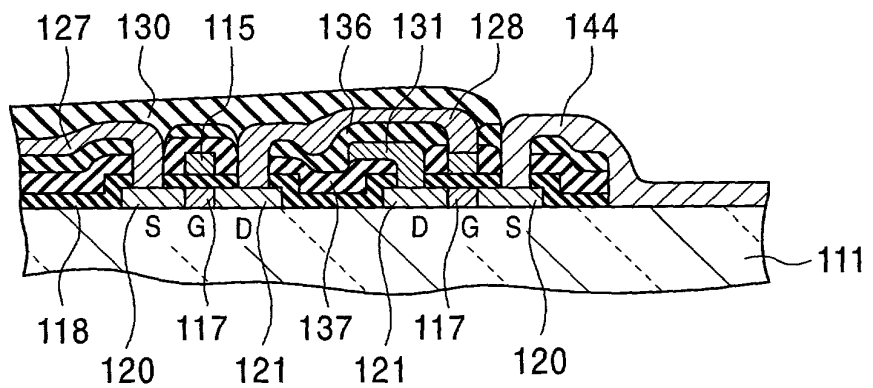
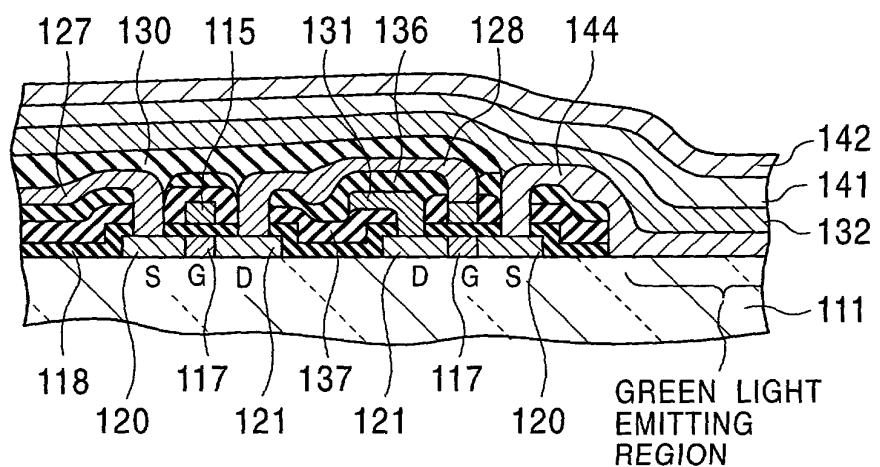


FIG. 22D



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FIG. 23A

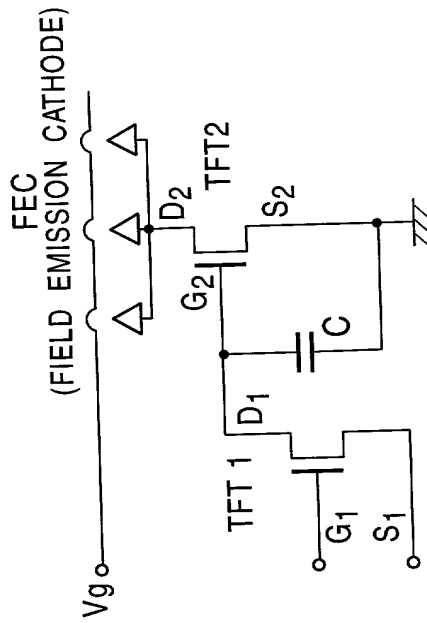


FIG. 23C

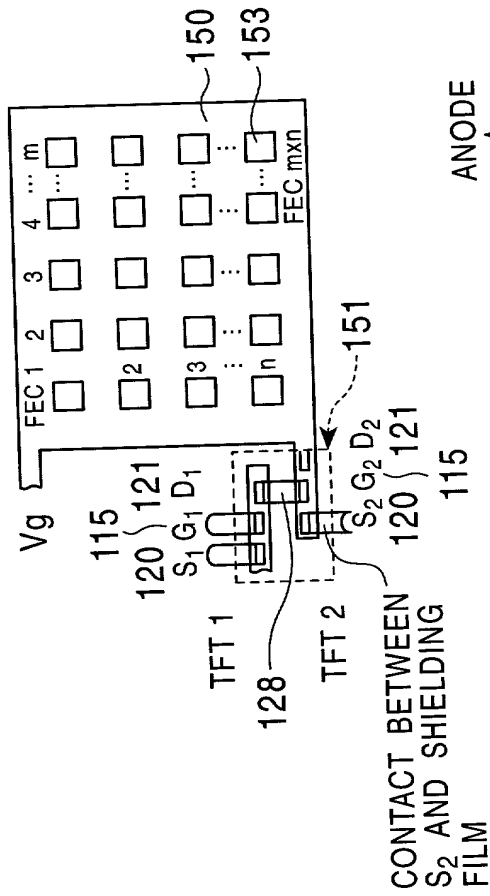


FIG. 23B

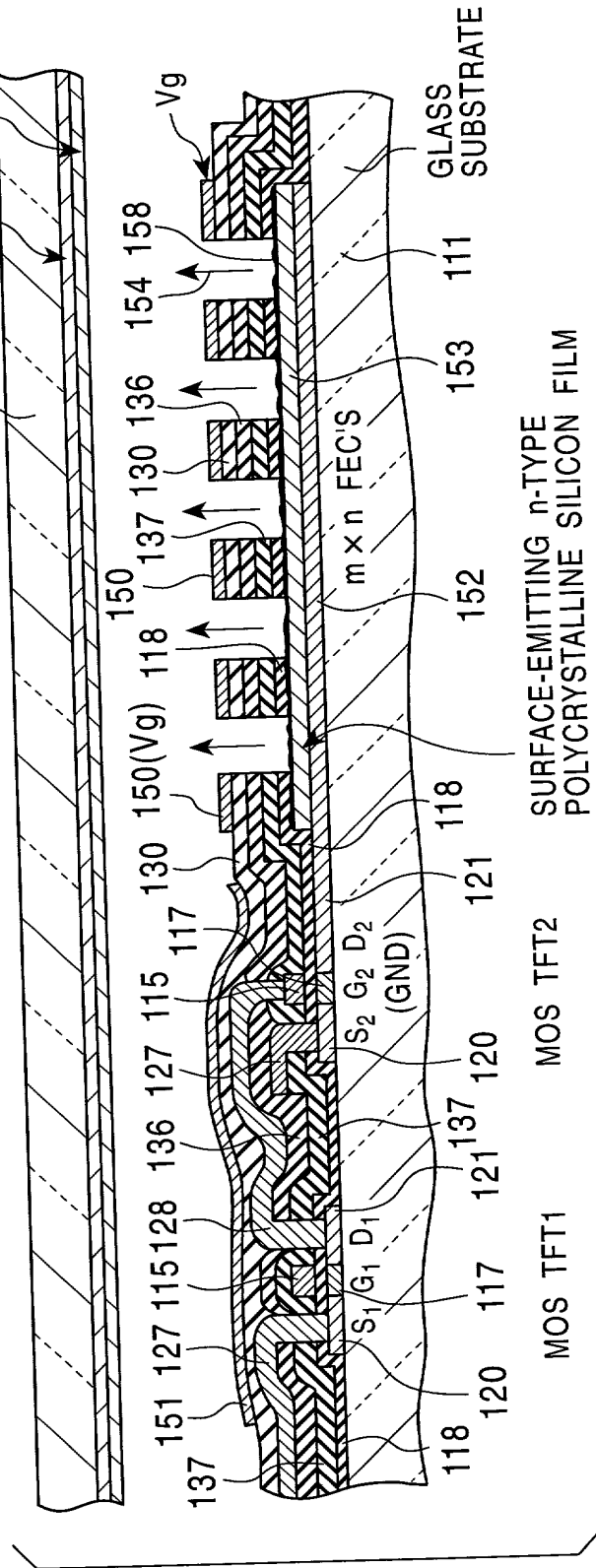


FIG. 24A

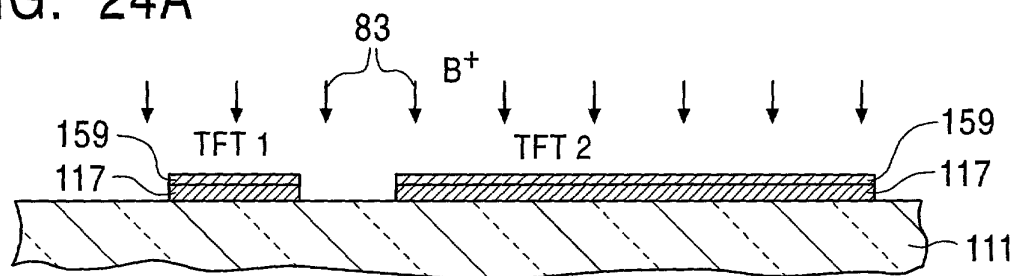


FIG. 24B

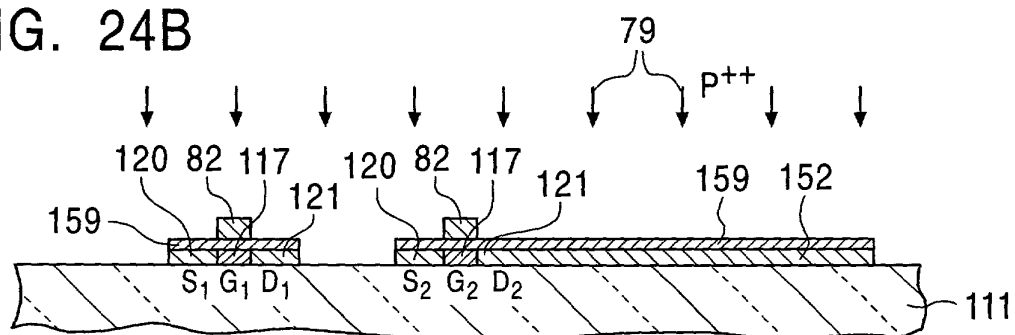


FIG. 24C

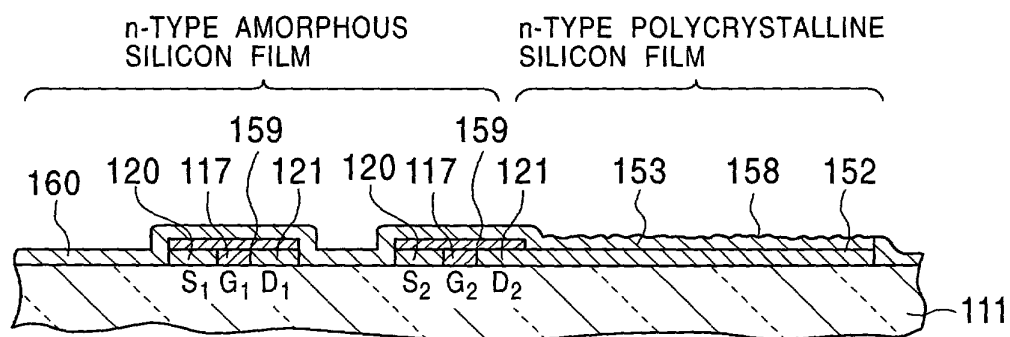
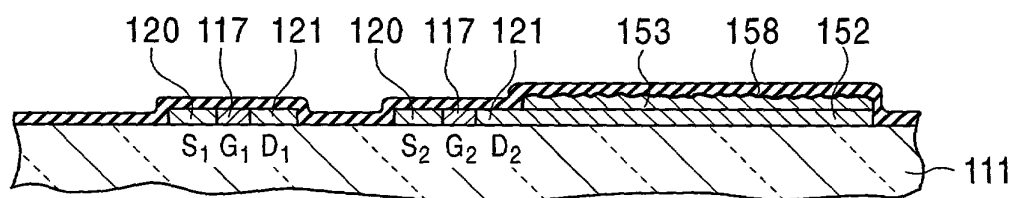


FIG. 24D



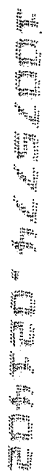
A cross-sectional view of a semiconductor device. The device consists of a substrate 111 with a top layer 118. Below the top layer 118 is a layer 115. Within layer 115, there are regions labeled S_1 , G_1 , and D_1 on the left, and S_2 , G_2 , and D_2 in the middle. Above these regions are gate structures 120 and 121. To the right of the gate structures is a region 137, followed by a layer 136, and a top layer 158. The bottom of the device is labeled 152 and 153. The top surface of the device is labeled 115 and 127.

This cross-sectional view shows a multi-layered semiconductor structure. The top layer consists of several regions with different hatching patterns, labeled 127, 115, 128, 127, 115, 136, 137, and 158. Below this top layer is a middle layer divided into sections labeled S_1 , G_1 , D_1 , S_2 , G_2 , and D_2 . The bottom layer is a continuous substrate labeled 120. Other labels include 117, 121, 152, 153, 111, and 118, which point to various interfaces and regions within the device structure.

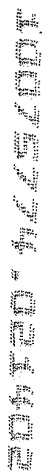
A cross-sectional view of a semiconductor device. The device consists of a substrate 111 with a top layer 118. A series of layers are deposited on top of 118, including a layer 120 with regions 121 and 122. A layer 127 is deposited on top of 120, with regions 127 and 128. A layer 115 is deposited on top of 127, with regions 115 and 116. A layer 136 is deposited on top of 115, with regions 136 and 137. A layer 130 is deposited on top of 136, with regions 130 and 131. A layer 137 is deposited on top of 130, with regions 137 and 138. A layer 158 is deposited on top of 137, with regions 158 and 159. The regions 120, 121, 122, 127, 128, 115, 116, 136, 137, 130, 131, 137, 158, 159, 120, 117, 121, 152, 153, 111, and 118 are labeled with reference numerals.

[illegible]

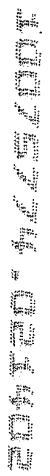
SURFACE-EMITTING FEC
FORMED OF AN n-TYPE
POLYCRYSTALLINE SILICON FILM

[illegible]

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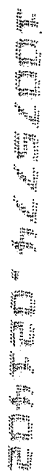


FIG. 26E

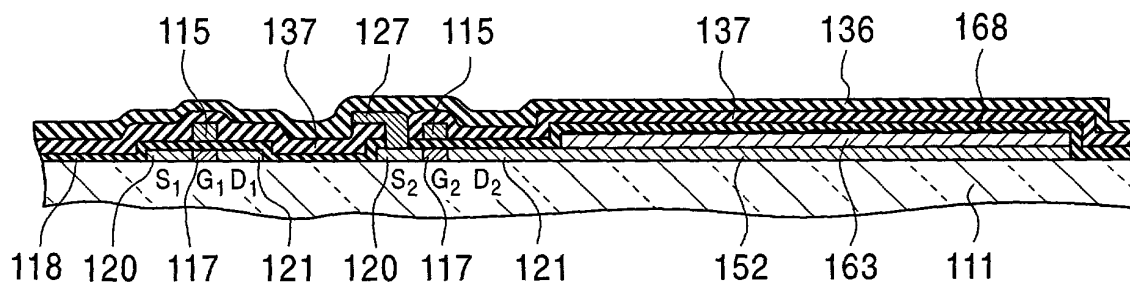


FIG. 26F

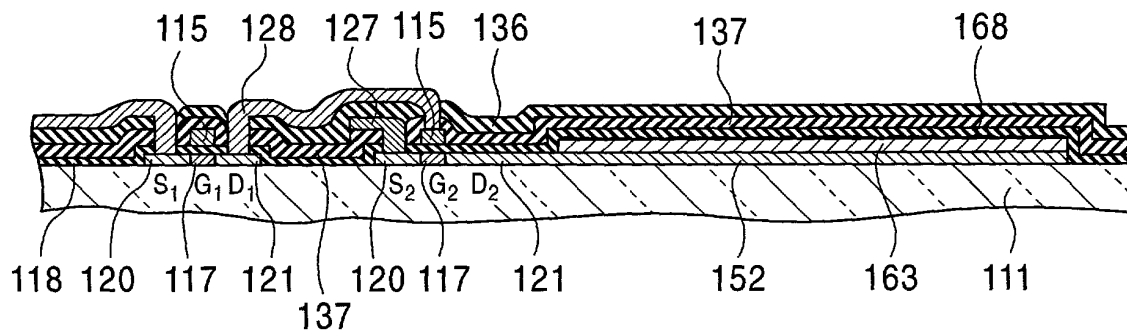


FIG. 26G

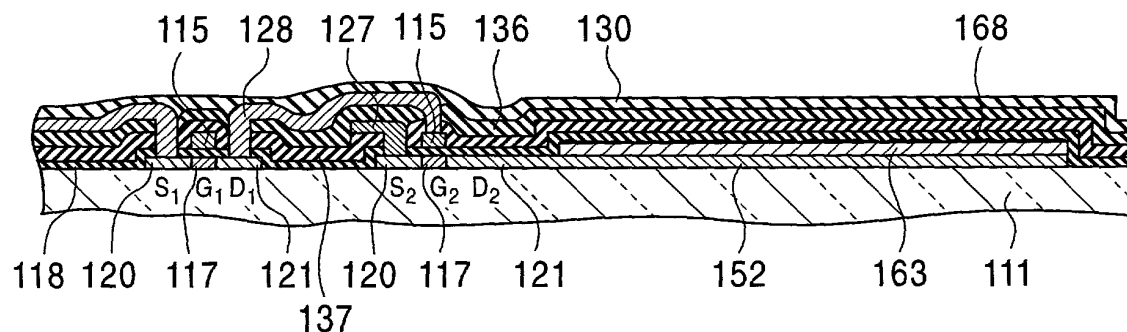


FIG. 26H

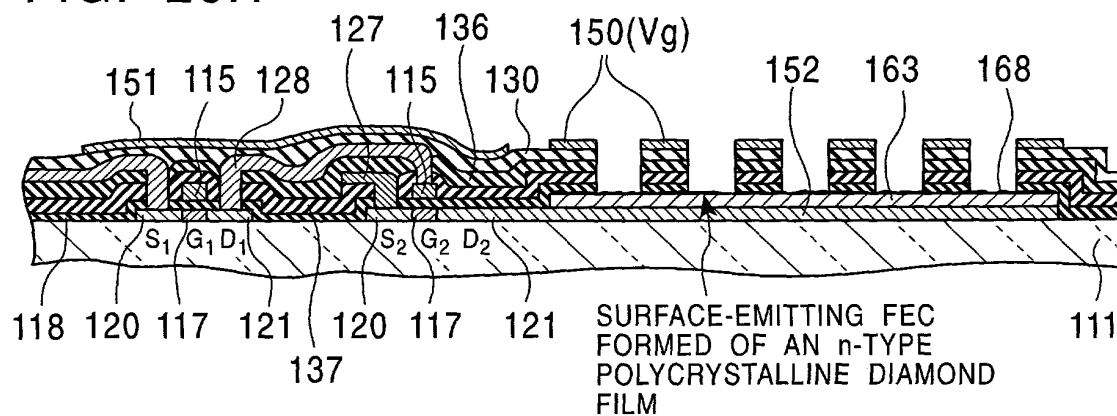


FIG. 27A

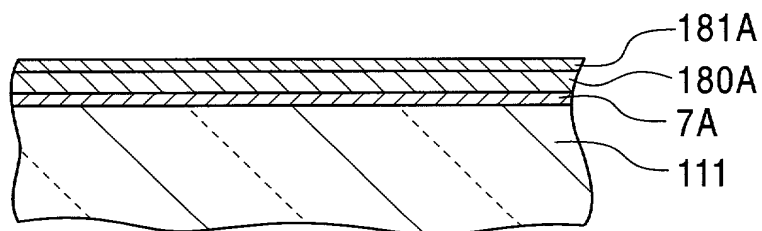


FIG. 27B

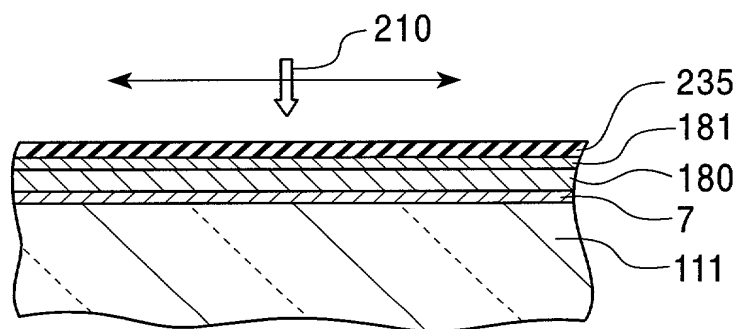


FIG. 27C

